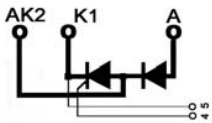


# ST8 116GKXXB

## Thyristor-8 ]cXY Modules

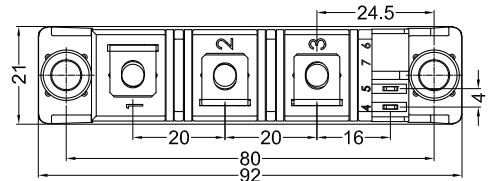
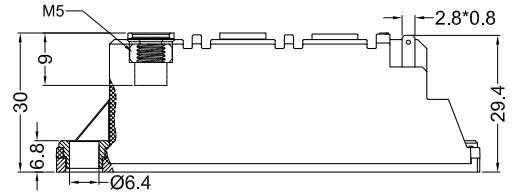


STD\*\*B

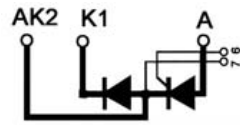


Type	$V_{RSM}$ $V_{DSM}$ V	$V_{RRM}$ $V_{DRM}$ V
ST8 116GK08B	900	800
ST8 116GK12B	1300	1200
ST8 116GK14B	1500	1400
ST8 116GK16B	1700	1600
ST8 116GK18B	1900	1800

Dimensions in mm (1mm=0.0394")



SDT\*\*B



Symbol	Test Conditions	Maximum Ratings	Unit
$I_{TRMS}$ , $I_{FRMS}$ $I_{TAVM}$ , $I_{FAVM}$	$T_{VJ}=T_{VJM}$ $T_C=85^{\circ}C$ ; 180° sine	180 116	A
$I_{TSM}$ , $I_{FSM}$	$T_{VJ}=45^{\circ}C$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	2250 2400	A
	$T_{VJ}=T_{VJM}$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	2000 2150	
$\int i^2 dt$	$T_{VJ}=45^{\circ}C$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	25300 23900	A <sup>2</sup> s
	$T_{VJ}=T_{VJM}$ $V_R=0$ $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	20000 19100	
$(di/dt)_{cr}$	$T_{VJ}=T_{VJM}$ $f=50Hz$ , $t_p=200\mu s$ $V_D=2/3V_{DRM}$ $I_G=0.45A$ $di_G/dt=0.45A/\mu s$ repetitive, $I_T=250A$	150	A/ $\mu s$
	non repetitive, $I_T=I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$ ; $R_{GK}=\infty$ ; method 1 (linear voltage rise) $V_{DR}=2/3V_{DRM}$	1000	V/ $\mu s$
$P_{GM}$	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$ $t_p=30\mu s$ $t_p=300\mu s$	10 5	W
		0.5	
$P_{GAV}$		10	W
$V_{RGM}$		10	V
$T_{VJ}$ $T_{VJM}$ $T_{stg}$		-40...+125 125 -40...+125	°C
$V_{ISOL}$	50/60Hz, RMS $I_{ISOL}\leq 1mA$ $t=1min$ $t=1s$	3000 3600	V~
$M_d$	Mounting torque (M5)	2.5-4.0/22-35	Nm/lb.in.
	Terminal connection torque (M5)	2.5-4.0/22-35	
Weight	Typical	110	g

**Sirectifier**®

# ST8 116GKXXB

## Thyristor-8 JcXY Modules

Symbol	Test Conditions	Characteristic Values	Unit
<b>I<sub>RRM</sub>, I<sub>DRM</sub></b>	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
<b>V<sub>TM</sub></b>	$I_{TM}=330A; T_{VJ}=25^{\circ}C$	1.50	V
<b>V<sub>TO</sub></b>	For power-loss calculations only ( $T_{VJ}=125^{\circ}C$ )	0.8	V
<b>r<sub>T</sub></b>		2.4	mΩ
<b>V<sub>GT</sub></b>	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	2.5 2.6	V
<b>I<sub>GT</sub></b>	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	150 200	mA
<b>V<sub>GD</sub></b>	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
<b>I<sub>GD</sub></b>		10	mA
<b>I<sub>L</sub></b>	$T_{VJ}=25^{\circ}C; t_p=10\mu s; V_D=6V$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	450	mA
<b>I<sub>H</sub></b>	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	200	mA
<b>t<sub>gd</sub></b>	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	2	us
<b>t<sub>q</sub></b>	$T_{VJ}=T_{VJM}; I_T=150A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$	185	us
<b>Q<sub>s</sub></b>	$T_{VJ}=T_{VJM}; I_T, I_F=50A; -di/dt=6A/\mu s$	170	uC
<b>I<sub>RM</sub></b>		45	A
<b>R<sub>thJC</sub></b>	per thyristor/diode; DC current per module	0.270 0.135	K/W
<b>R<sub>thJK</sub></b>	per thyristor/diode; DC current per module	0.470 0.235	K/W
<b>d<sub>s</sub></b>	Creeping distance on surface	12.7	mm
<b>d<sub>A</sub></b>	Strike distance through air	9.6	mm
<b>a</b>	Maximum allowable acceleration	50	m/s <sup>2</sup>

### FEATURES

- \* International standard package
- \* Copper base plate
- \* Glass passivated chips
- \* Isolation voltage 3600 V~
- \* UL file NO.E310749
- \* RoHS compliant

### APPLICATIONS

- \* DC motor control
- \* Softstart AC motor controller
- \* Light, heat and temperature control

### ADVANTAGES

- \* Space and weight savings
- \* Simple mounting with two screws
- \* Improved temperature and power cycling
- \* Reduced protection circuits

# ST8 116GKXXB

## Thyristor-8 ]cXY Modules

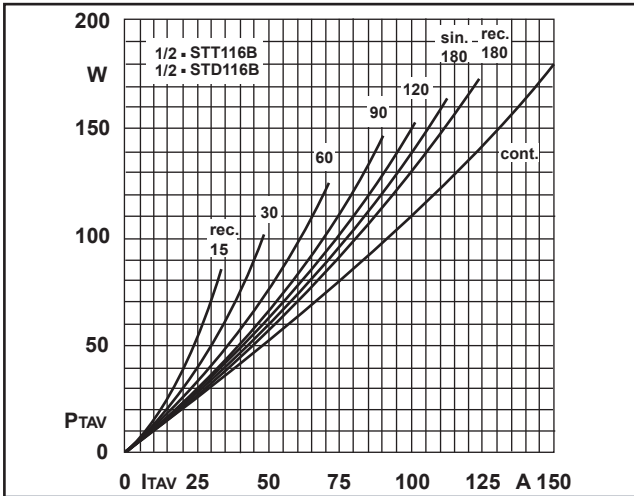


Fig.1L Power dissipation per thyristor vs. on-state current

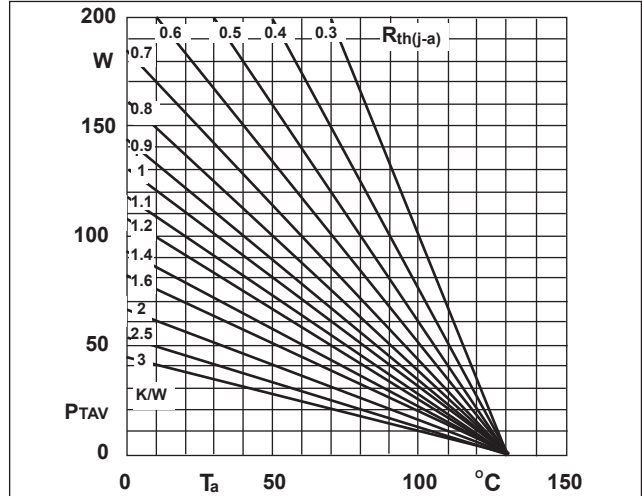


Fig.1R Power dissipation per thyristor vs. ambient temp

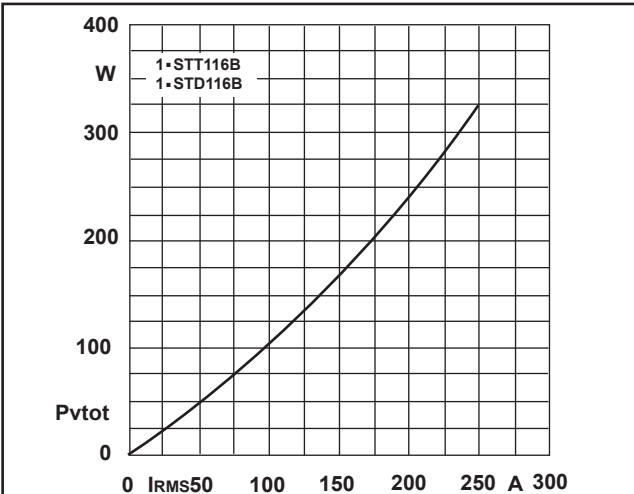


Fig.2L Power dissipation per module vs. rms current

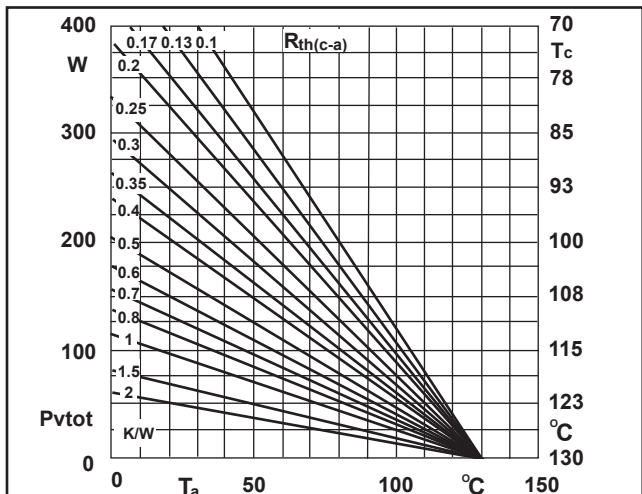


Fig.2R Power dissipation per module vs. case temp

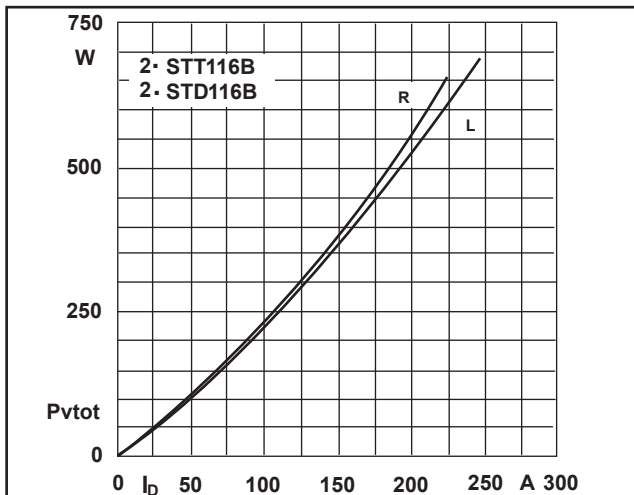


Fig.3L Power dissipation of two modules vs. direct current

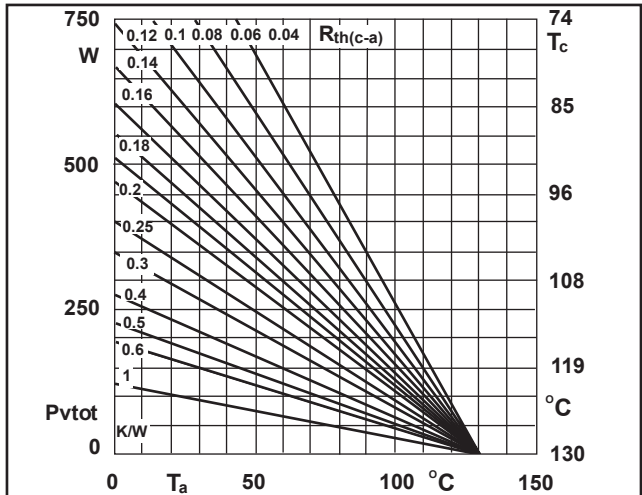


Fig.3 R Power dissipation of two modules vs. case temp

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## Thyristor-8 ]cXY Modules

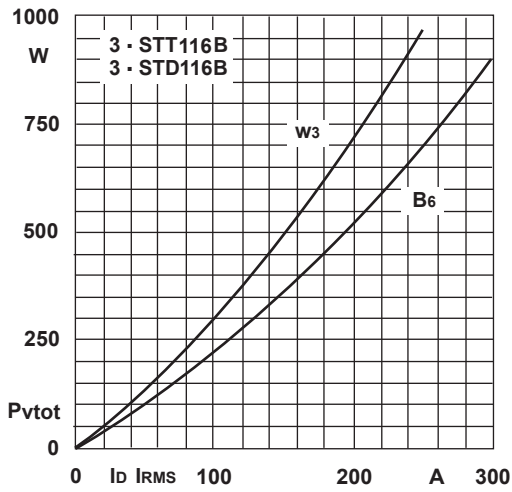


Fig.4L Power dissipation of three modules vs. direct and rms current

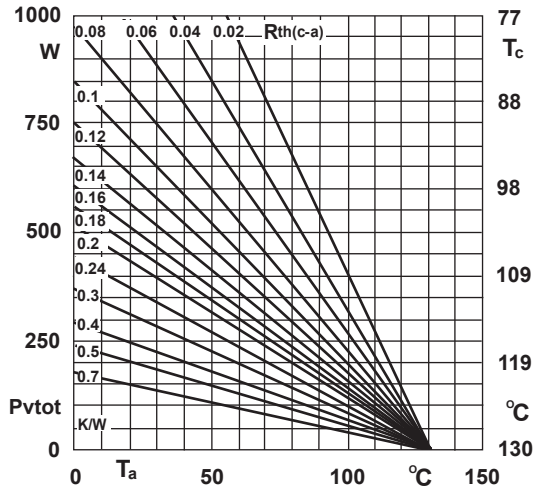


Fig.4R Power dissipation of three modules vs. case temp

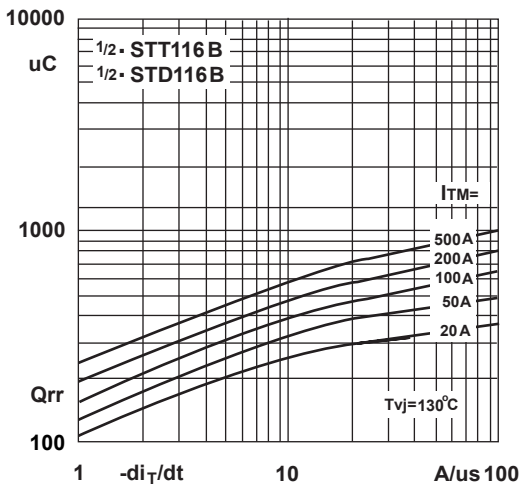


Fig.5 Recovered charge vs. current decrease

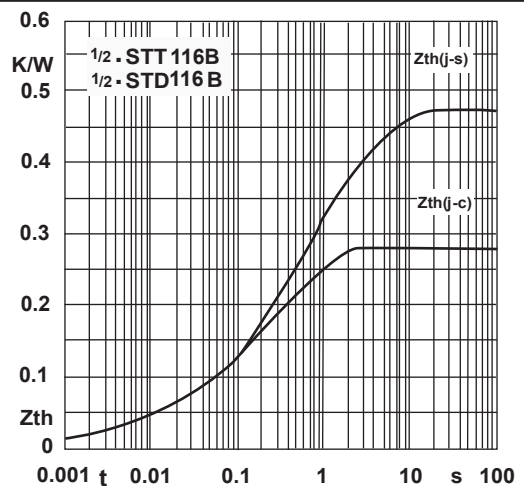


Fig.6 Transient thermal impedance vs. time

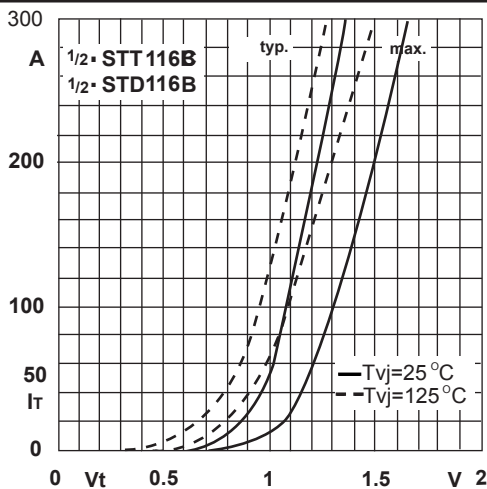


Fig.7 On-state characteristics

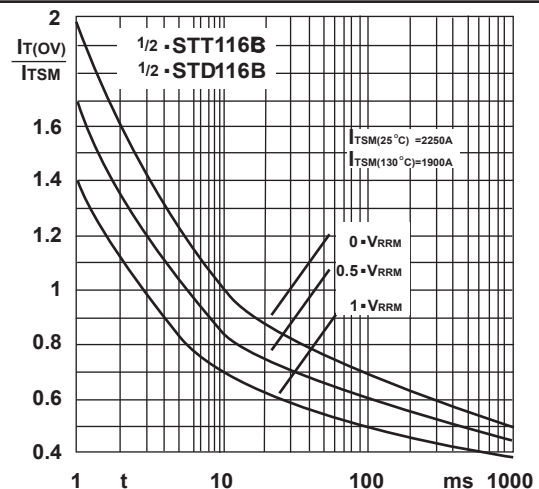


Fig.8 Surge overload current vs. time